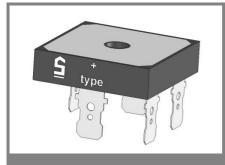
DB 35-005 ... DB 35-16



Square bridge

Three-Phase Si-Bridge Rectifiers

DB 35-005 ... DB 35-16 Forward Current: 35 A

Reverse Voltage: 50 to 1600 V

Publish Data

Features

- Max. solder temperature: 260 °C, max. 5s
- UL recognized, file no. E63532
- V_{ISO} > 2500 V

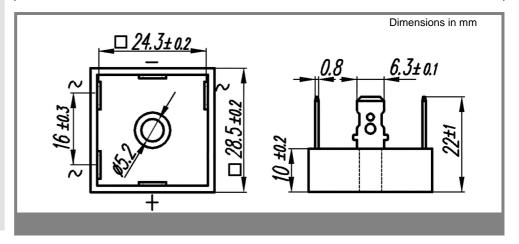
Mechanical Data

- Plastic case with alu-bottom
- Dimensions: 28,5 28,5 10 mm
- Weight approx. 23 g
- Standard packaging: bulk
- Terminals: plated terminals solderable per IEC 68-2-20
- · Mounting position: any
- Admissible torque for mounting (M 5): 2 (± 10%) Nm

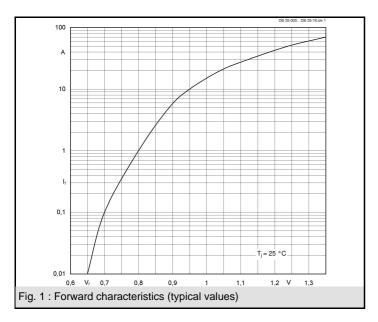
Туре	Alternating input voltage V _{RMS} V	Repetetive peak reverse voltage V _{RRM} V
DB 35-005	35	50
DB 35-01	70	100
DB 35-02	140	200
DB 35-04	280	400
DB 35-06	420	600
DB 35-08	560	800
DB 35-10	700	1000
DB 35-12	800	1200
DB 35-14	900	1400
DB 35-16	1000	1600

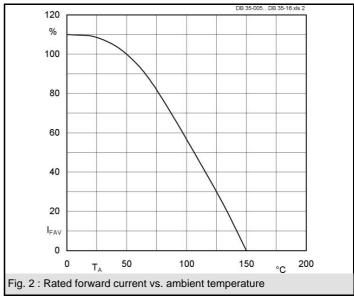
Absolute Maximum Ratings T _c = 25 °C unless otherwise specified				
Symbol	Conditions	Values	Units	
I _{FRM}	Repetitive peak forward current; f > 15 Hz ¹⁾	120	Α	
l²t	Rating for fusing, t < 10 ms	1000	A²s	
I _{FSM}	Peak forward surge current, 50 Hz half sine-wave $T_{\rm A}$ = 25 °C	450	Α	
I _{FAV}	Max. averaged fwd. current, R-load, T _A = 50 °C ¹⁾	not applicable	А	
I _{FAV}	Max. averaged fwd. current, C-load, T _A = 50 °C ¹⁾	not applicable	А	
I _{FAV}	Max. current with cooling fin, R-load, T _C = 100 °C ²⁾	35	А	
I _{FAV}	Max. current with cooling fin, C-load, T _C = 100 °C ²⁾	35	А	
R _{thA}	Thermal resistance junction to ambient 1)		K/W	
R _{thC}	Thermal resistance junction to case 1)	1,8	K/W	
T _j	Operating junction temperature	- 50 + 150 °C	°C	
T _s	Storage temperature	- 50 + 150 °C	°C	

Characteristics $T_c = T_c$		5 °C unless otherwise specified	
Symbol	Conditions	Values	Units
V _F	Maximum forward. voltage, $T_j = 25 \text{ °C; } I_F = 17,5 \text{ A}$	1,05	V
I _R	Maximum Leakage current, $T_j = 25 \text{ °C; } V_R = V_{RRM}$	10	μΑ
CJ	Typical junction capacitance per leg at V, MHz		pF



DB 35-005 ... DB 35-16





2 23-03-2005 SCT © by SEMIKRON